

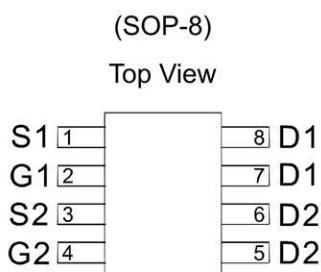
## GENERAL FEATURES

- $R_{DS(ON)} \leq 35 \text{ m}\Omega$  @  $V_{GS}=10V$
- $R_{DS(ON)} \leq 45 \text{ m}\Omega$  @  $V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

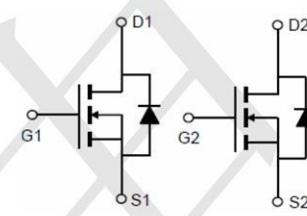
## Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

## Package and Pin Configuration

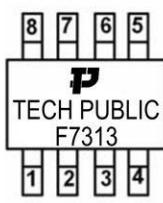


Circuit diagram



Schematic diagram

## Marking:



## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter                               | Symbol          | Maximum Ratings | Unit |
|---|-----------------|-----------------|------|
| Drain-Source Voltage                    | $V_{DS}$        | 30              | V    |
| Gate-Source Voltage                     | $V_{GS}$        | $\pm 20$        | V    |
| Continuous Drain Current                | $I_D$           | 7               | A    |
|   |                 | 4.8             |      |
| Pulsed Drain Current                    | $I_{DM}$        | 24              | A    |
| Maximum Power Dissipation               | $P_D$           | 2               | W    |
|   |                 | 1.3             |      |
| Operating Junction Temperature          | $T_J$           | -55 to 150      | °C   |
| Thermal Resistance-Junction to Ambient* | $R_{\theta JA}$ | 62.5            | °C/W |

**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

| Symbol                      | Parameter                       | Limit  | Min | Typ  | Max       | Unit             |
|-----------------------------|---------------------------------|--|-----|------|-----------|------------------|
| <b>STATIC</b>               |                                 |  |     |      |           |                  |
| $V_{(\text{BR})\text{DSS}}$ | Drain-Source Breakdown Voltage  | $V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\ \mu\text{A}$   | 30  |      |           | V                |
| $V_{\text{GS}(\text{th})}$  | Gate Threshold Voltage          | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\ \mu\text{A}$   | 1   |      | 3         | V                |
| $I_{\text{GSS}}$            | Gate Leakage Current            | $V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 20\text{V}$  |     |      | $\pm 100$ | nA               |
| $I_{\text{DSS}}$            | Zero Gate Voltage Drain Current | $V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$  |     |      | 1         | $\mu\text{A}$    |
| $R_{\text{DS}(\text{ON})}$  | Drain-Source On-Resistance      | $V_{\text{GS}}=10\text{V}, I_{\text{D}}=6.9\text{A}$   |     | 18   | 35        | $\text{m}\Omega$ |
|                             |                                 | $V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=5.8\text{A}$  |     | 24   | 45        |                  |
| $V_{\text{SD}}$             | Diode Forward Voltage           | $I_{\text{S}}=1.7\text{A}, V_{\text{GS}}=0\text{V}$  |     | 0.75 | 1.2       | V                |
| <b>DYNAMIC</b>              |                                 |  |     |      |           |                  |
| $Q_g$                       | Total Gate Charge               | $V_{\text{DS}}=15\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=6.9\text{A}$   |     | 11.5 |           | nC               |
| $Q_{\text{gs}}$             | Gate-Source Charge              |  |     | 2.7  |           |                  |
| $Q_{\text{gd}}$             | Gate-Drain Charge               |  |     | 2.3  |           |                  |
| $C_{\text{iss}}$            | Input Capacitance               | $V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$   |     | 350  |           | pF               |
| $C_{\text{oss}}$            | Output Capacitance              |  |     | 65   |           |                  |
| $C_{\text{rss}}$            | Reverse Transfer Capacitance    |  |     | 16   |           |                  |
| $t_{\text{d(on)}}$          | Turn-On Delay Time              | $V_{\text{DD}}=15\text{V}, R_{\text{L}}=15\Omega$<br>$I_{\text{D}}=1\text{A}, V_{\text{GEN}}=10\text{V}$<br>$R_{\text{G}}=6\Omega$ |     | 9    |           | ns               |
| $t_r$                       | Turn-On Rise Time               |  |     | 10   |           |                  |
| $t_{\text{d(off)}}$         | Turn-Off Delay Time             |  |     | 32   |           |                  |
| $t_f$                       | Turn-Off Fall Time              |  |     | 3.5  |           |                  |



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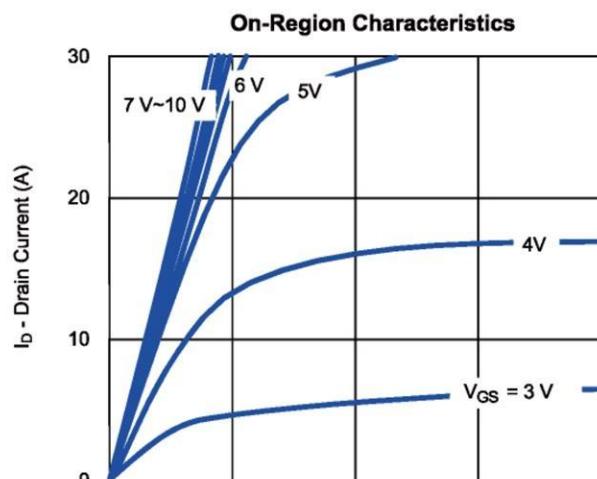
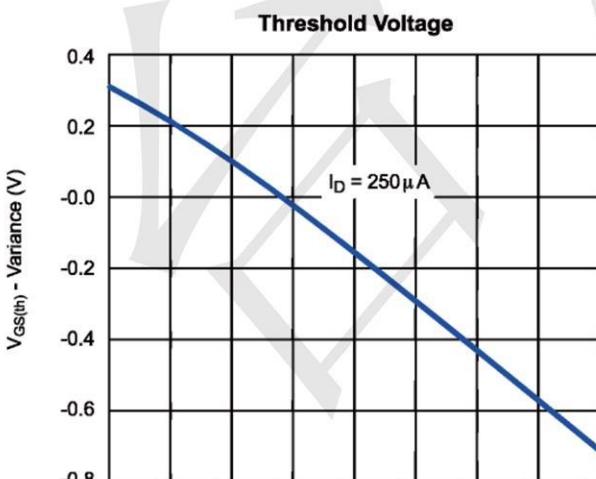
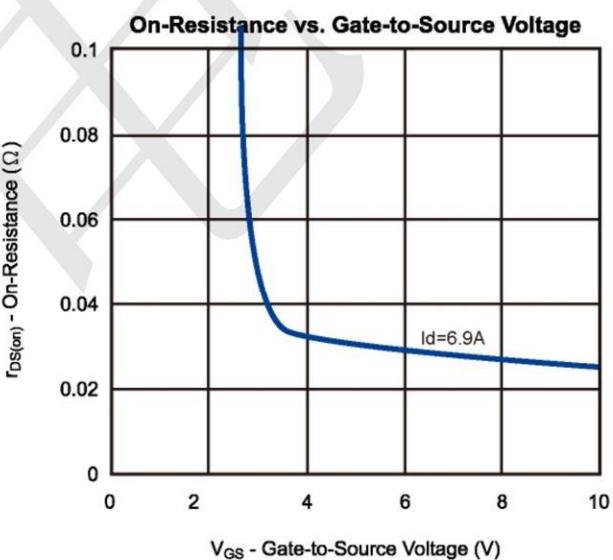
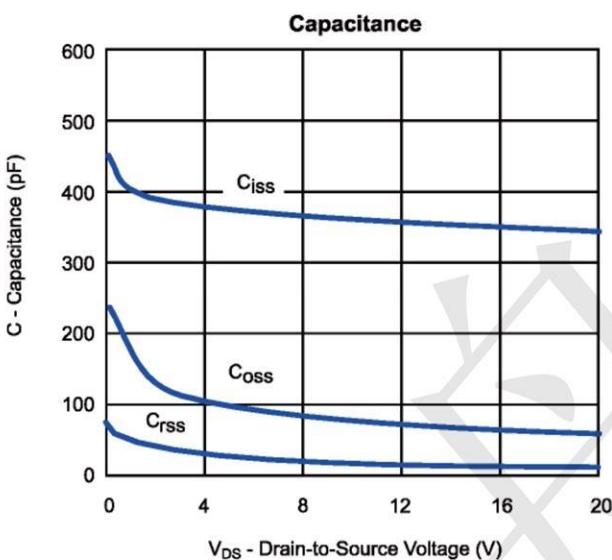
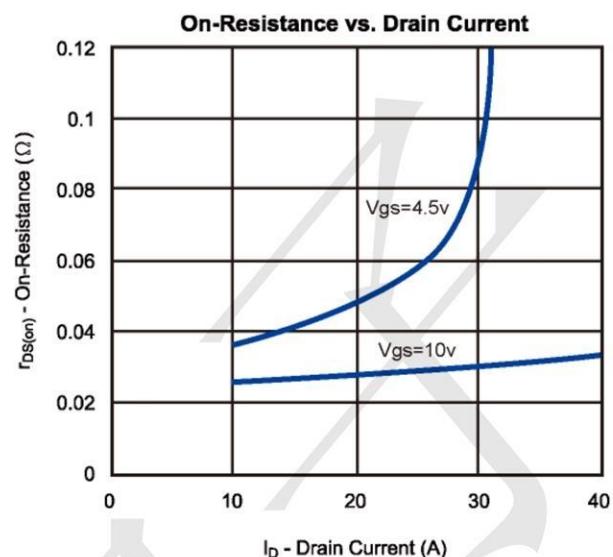
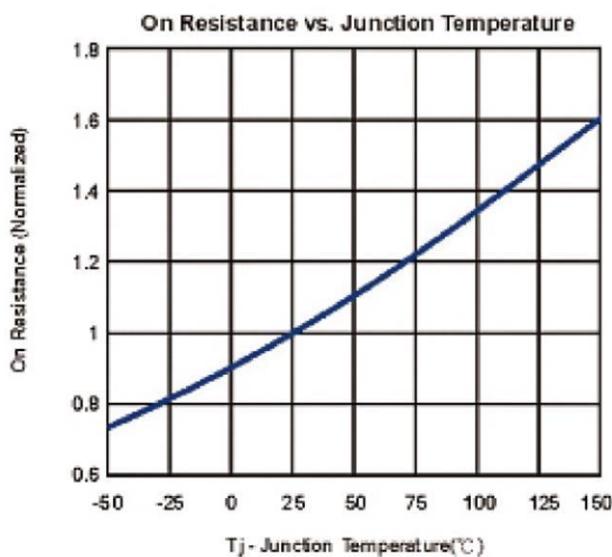
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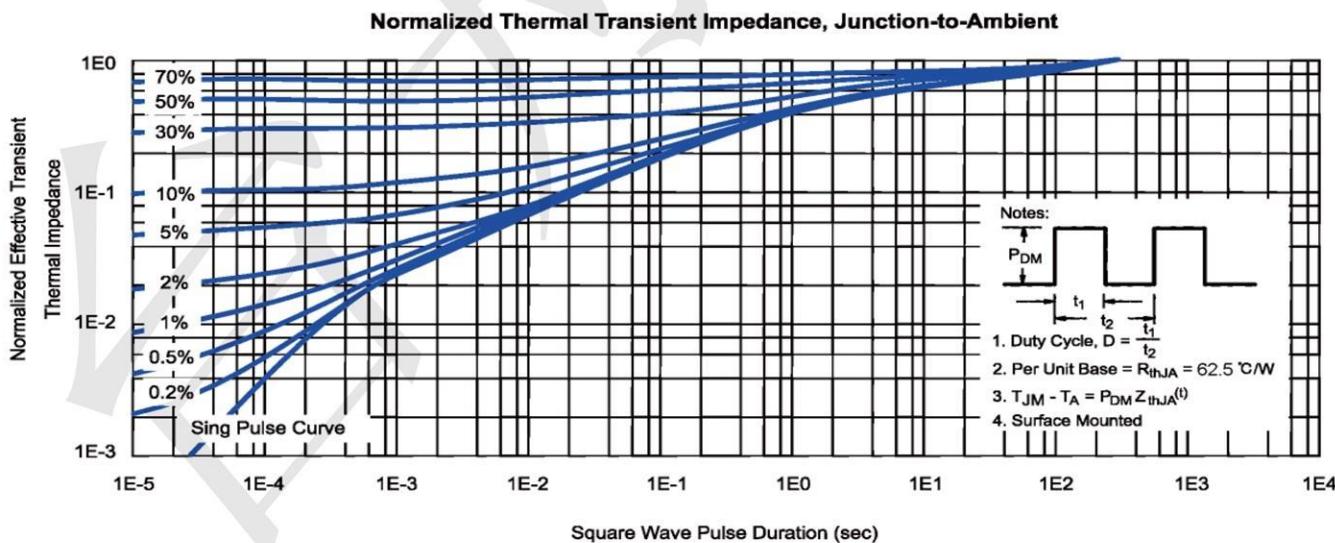
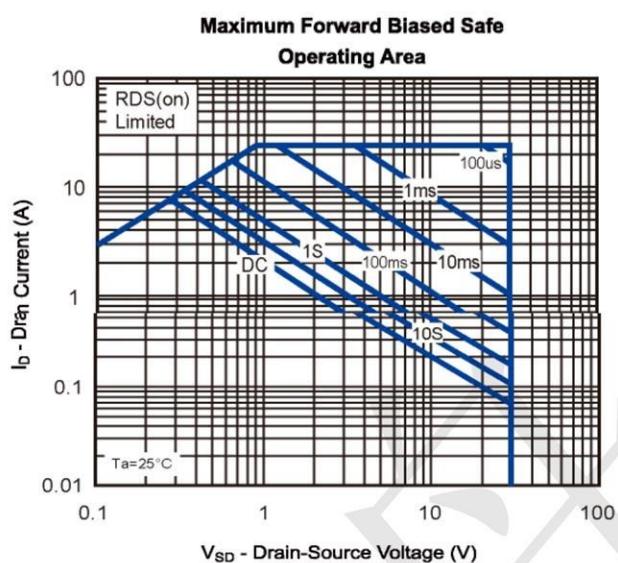
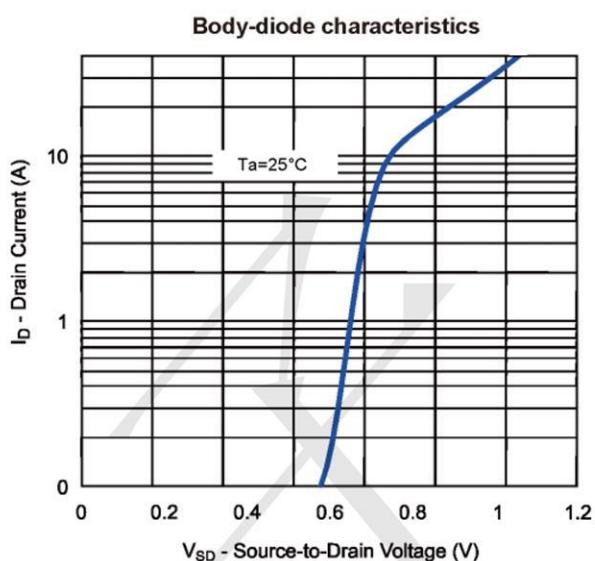
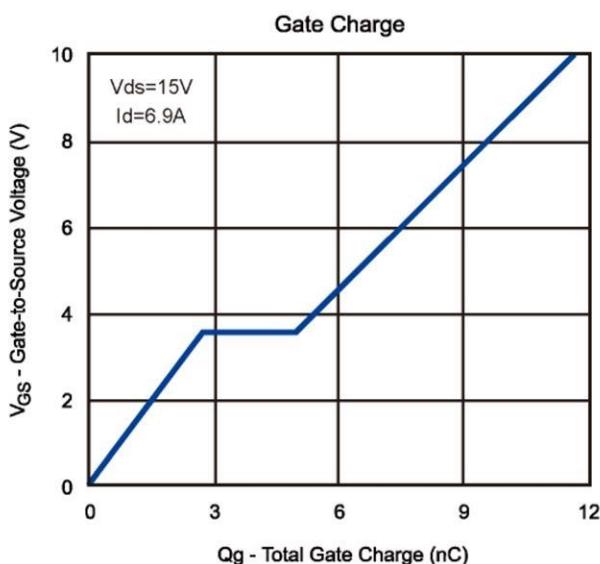
**IRF7313TRPBF**

Dual N-Channel Enhancement Mode Power MOSFET

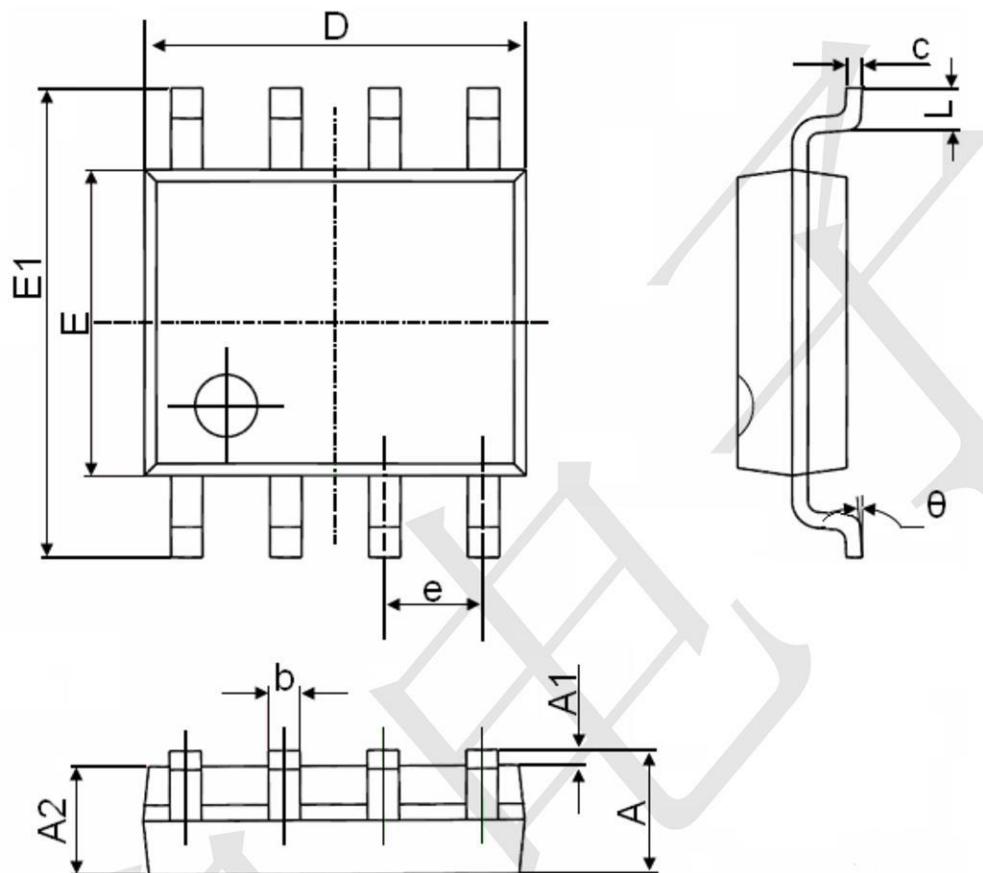
[www.sot23.com.tw](http://www.sot23.com.tw)

### Typical Electrical and Thermal Characteristics





### SOP-8 Package Information



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min.                      | Max.  | Min.                 | Max.  |
| A      | 1.350                     | 1.750 | 0.053                | 0.069 |
| A1     | 0.100                     | 0.250 | 0.004                | 0.010 |
| A2     | 1.350                     | 1.550 | 0.053                | 0.061 |
| b      | 0.330                     | 0.510 | 0.013                | 0.020 |
| c      | 0.170                     | 0.250 | 0.006                | 0.010 |
| D      | 4.700                     | 5.100 | 0.185                | 0.200 |
| E      | 3.800                     | 4.000 | 0.150                | 0.157 |
| E1     | 5.800                     | 6.200 | 0.228                | 0.244 |
| e      | 1.270(BSC)                |       | 0.050(BSC)           |       |
| L      | 0.400                     | 1.270 | 0.016                | 0.050 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |